

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ Max}$	$I_D \text{ Max}$ $T_A = +25^\circ\text{C}$
-30V	10mΩ @ $V_{GS} = -10V$	-11.5A
	18mΩ @ $V_{GS} = -4.5V$	-8.7A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

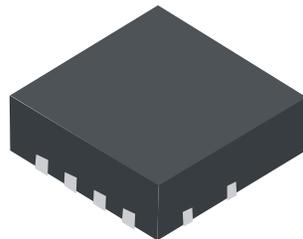
Features and Benefits

- Low $R_{DS(ON)}$ – Ensures On-State Losses Are Minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP capable (Note 4)**

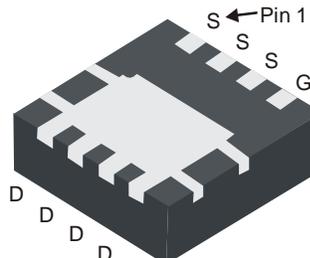
Mechanical Data

- Case: POWERDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 Ⓔ3
- Weight: 0.072 grams (Approximate)

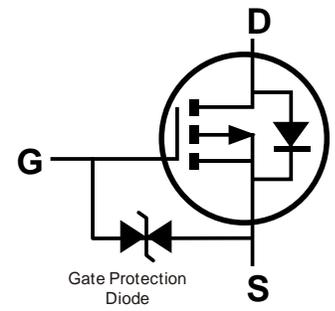
POWERDI3333-8



Top View



Bottom View



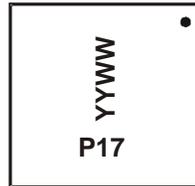
Equivalent Circuit

Ordering Information (Note 5)

Part Number	Case	Packaging
DMP3017SFGQ-7	POWERDI3333-8	2,000/Tape & Reel
DMP3017SFGQ-13	POWERDI3333-8	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
 5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

Marking Information



P17= Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last digit of year (ex: 13 = 2013)
 WW = Week code (01 ~ 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V _{DSS}	-30	V	
Gate-Source Voltage		V _{GSS}	±25	V	
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	I _D	T _A = +25°C T _A = +70°C	-11.5 -9.4	A
	t < 10s		T _A = +25°C T _A = +70°C	-15.2 -12.1	A
Maximum Continuous Body Diode Forward Current (Note 6)		I _S	-3.0	A	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)		I _{DM}	-80	A	
Avalanche Current (Note 8) L = 1mH		I _{AR}	14	A	
Repetitive Avalanche Energy (Note 8) L = 1mH		E _{AR}	104	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	0.94	W
	T _A = +70°C		0.6	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	137	°C/W
	t < 10s		82	°C/W
Total Power Dissipation (Note 7)	T _A = +25°C	P _D	2.2	W
	T _A = +70°C		1.3	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	R _{θJA}	60	°C/W
	t < 10s		36	°C/W
Thermal Resistance, Junction to Case (Note 7)		R _{θJC}	3.0	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout, please see <http://www.diodes.com/datasheets/ap02001.pdf> for latest version.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
 - I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep T_J = +25°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±25V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(th)}	-1.0	—	-3.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	8.5	10	mΩ	V _{GS} = -10V, I _D = -11.5A
		—	15	18		V _{GS} = -4.5V, I _D = -8.5A
Forward Transfer Admittance	Y _{fs}	—	24	—	S	V _{DS} = -5V, I _D = -11.5A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	2246	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	352	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	294	—	pF	
Gate resistance	R _g	—	5.1	12	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 5V)	Q _g	—	20.5	—	nC	V _{DS} = -15V, I _D = -11.5A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	41	—	nC	
Gate-Source Charge	Q _{gs}	—	7.6	—	nC	
Gate-Drain Charge	Q _{gd}	—	8.0	—	nC	
Turn-On Delay Time	t _{D(on)}	—	7.5	—	nS	V _{DD} = -15V, V _{GS} = -10V, R _G = 6Ω, I _D = -11.5A
Turn-On Rise Time	t _r	—	15.4	—	nS	
Turn-Off Delay Time	t _{D(off)}	—	45.6	—	nS	
Turn-Off Fall Time	t _f	—	36.8	—	nS	
BODY DIODE CHARACTERISTICS						
Diode Forward Voltage	V _{SD}	—	-0.7	—	V	V _{GS} = 0V, I _S = -1A
Reverse Recovery Time (Note 9)	t _{rr}	—	20	—	nS	I _S = -11.5A, dI/dt = 100A/μs
Reverse Recovery Charge (Note 9)	Q _{rr}	—	9.5	—	nC	

Notes: 9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

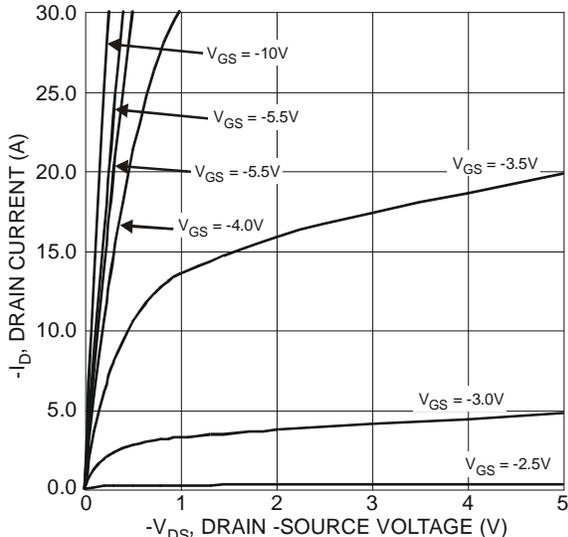


Figure 1 Typical Output Characteristics

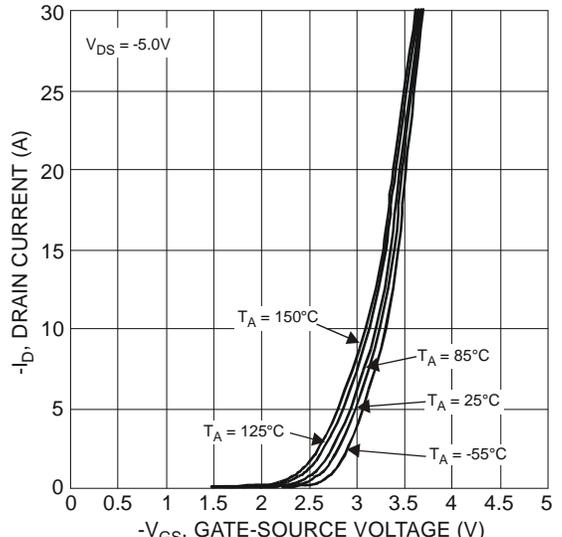


Figure 2 Typical Transfer Characteristics

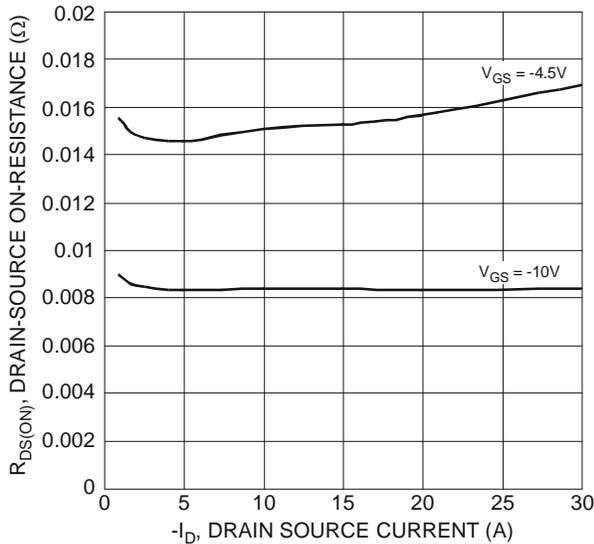


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

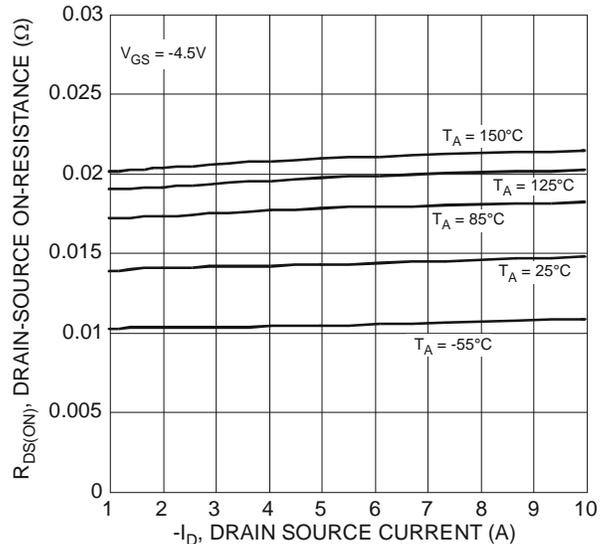


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

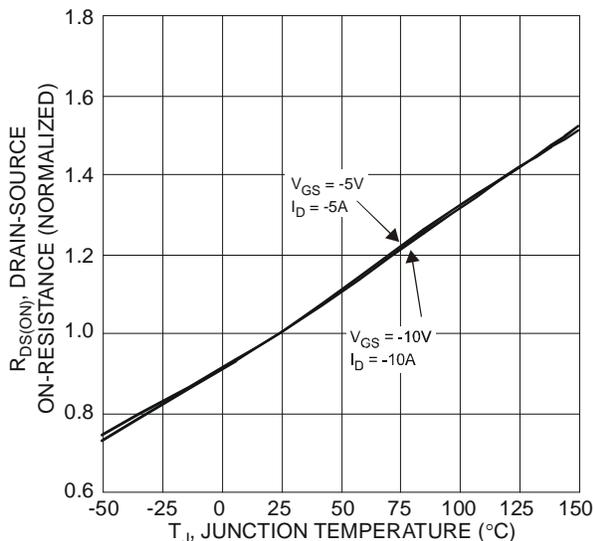


Figure 5 On-Resistance Variation with Temperature

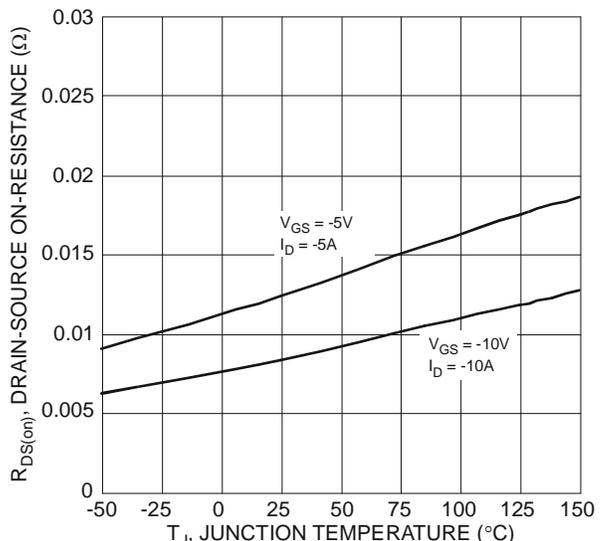


Figure 6 On-Resistance Variation with Temperature

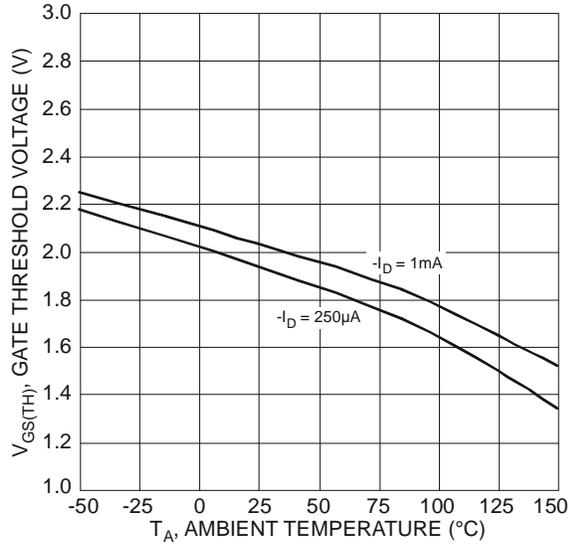


Figure 7 Gate Threshold Variation vs. Ambient Temperature

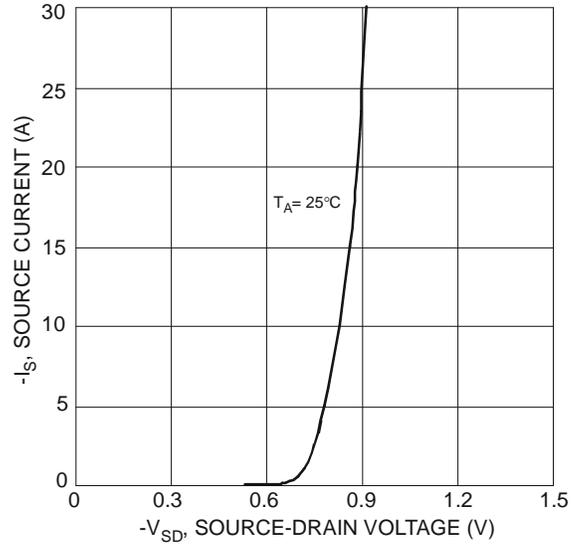


Figure 8 Diode Forward Voltage vs. Current

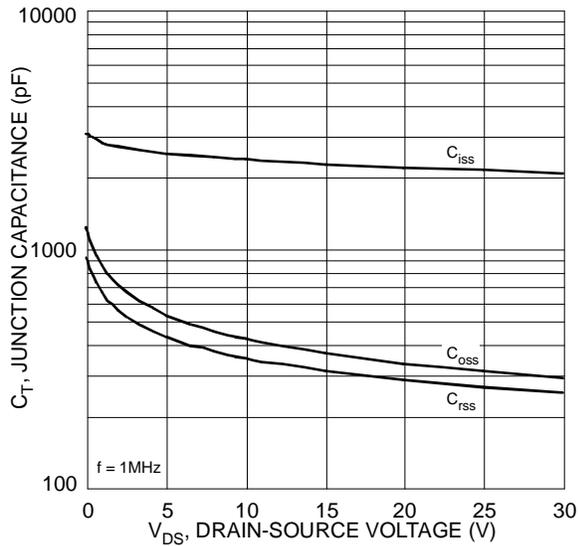


Figure 9 Typical Junction Capacitance

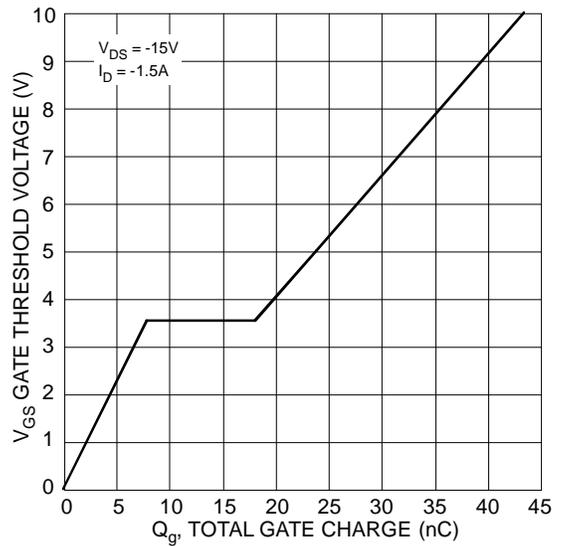


Figure 10 Gate Charge

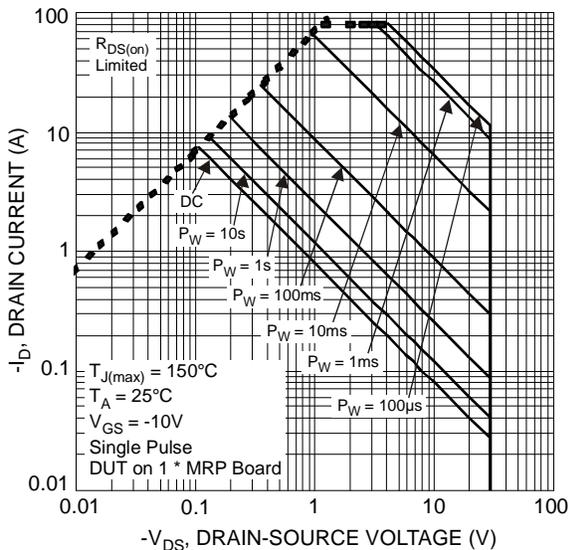
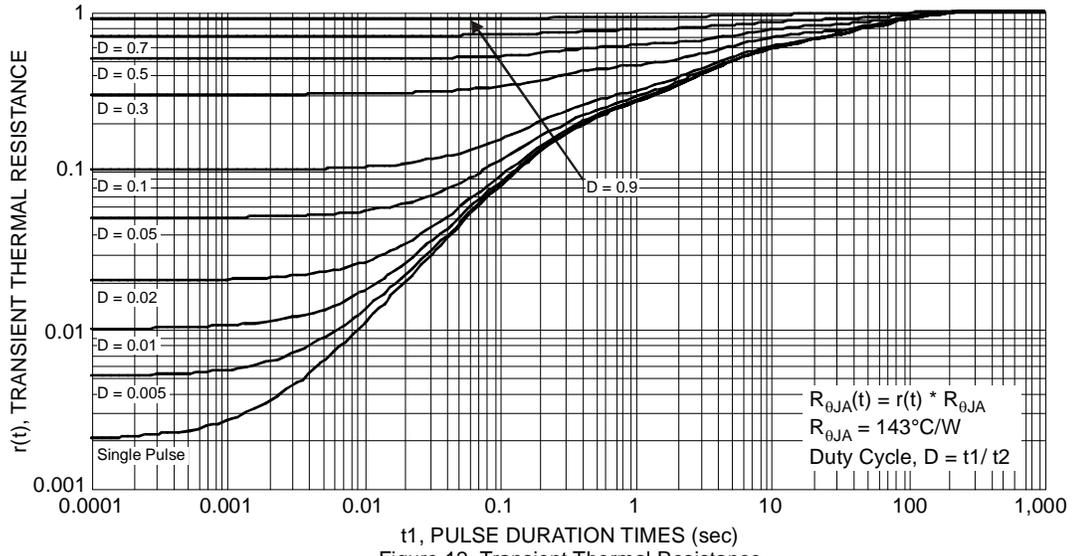
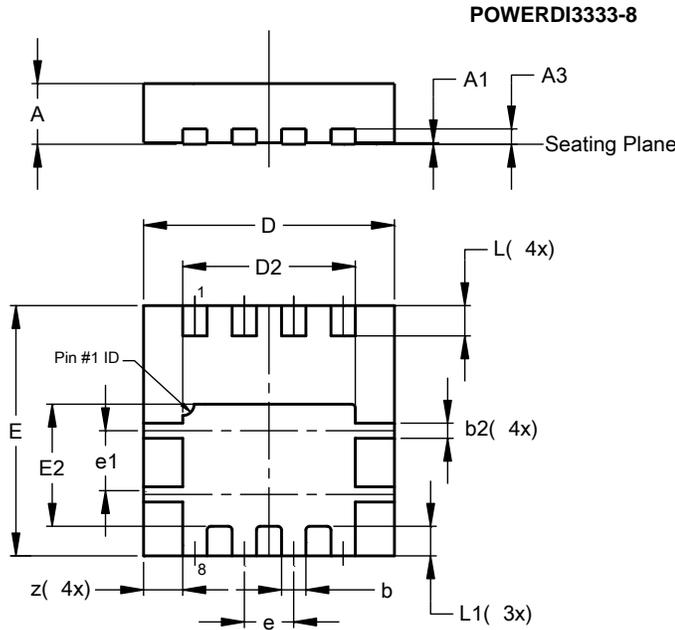


Figure 11 SOA, Safe Operation Area



Package Outline Dimensions

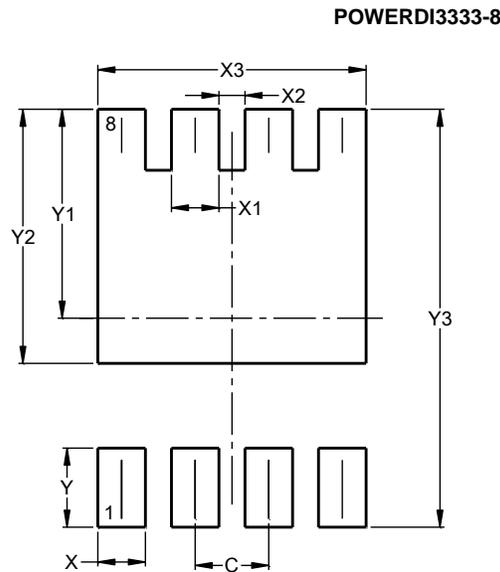
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



POWERDI [®] 3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	–	–	0.203
b	0.27	0.37	0.32
b2	–	–	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
e	–	–	0.65
e1	0.79	0.89	0.84
L	0.35	0.45	0.40
L1	–	–	0.39
z	–	–	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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